

Title (en)

METHOD FOR MANUFACTURING A MONOCRYSTALLINE LAYER OF DIAMOND OR IRIIDIUM MATERIAL, AND SUBSTRATE FOR EPITAXIALLY GROWING A MONOCRYSTALLINE LAYER OF DIAMOND OR IRIIDIUM MATERIAL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER MONOKRISTALLINEN SCHICHT AUS DIAMANT ODER IRIIDIUM UND SUBSTRAT ZUM EPITAKTISCHEN ZÜCHTEN EINER MONOKRISTALLINEN SCHICHT AUS DIAMANT ODER IRIIDIUM

Title (fr)

PROCÉDÉ DE FABRICATION D'UNE COUCHE MONOCRISTALLINE DE MATÉRIAU DIAMANT OU IRIIDIUM ET SUBSTRAT POUR CROISSANCE PAR ÉPITAXIE D'UNE COUCHE MONOCRISTALLINE DE MATÉRIAU DIAMANT OU IRIIDIUM

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Application

**EP 19721378 A 20190326**

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Abstract (en)

[origin: WO2019186262A1] Method for manufacturing a monocrystalline layer of diamond or iridium material, including transferring a monocrystalline seed layer of SrTiO<sub>3</sub> material onto a support substrate of silicon material, followed by epitaxially growing the monocrystalline layer of diamond or iridium material.

IPC 8 full level

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CPC (source: EP KR US)

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